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International Bureau

INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification 7 : C30B 15/10, 15/00, 29/06 — A1

(11) International Publication Number: WO 00/55395

(43) International Publication Date: 21 September 2000 (21.09.00)

(21) International Application Number: PCT/US00/06570

(22) International Filing Date: 14 March 2000 (14.03.00)

(30) Priority Data:

60/124,400	15 March 1999 (15.03.99)	US
09/521,525	8 March 2000 (08.03.00)	US

(81) Designated States: CN, JP, KR, SG, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).

Published
With international search report.

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(54) Title: STRONTIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS

(57) Abstract

A process for preparing strontium doped molten silicon for use in a single silicon crystal growing process is disclosed. Polysilicon is strontium and melted in a silica crucible. During melting and throughout the crystal growing process the strontium acts as a devitrification promoter and creates a layer of devitrified silica on the inside crucible surface in contact with the melt resulting in a lower level of contaminants in the melt and grown crystal.

